stop film layered in this order so that the second oxide etching stop film is formed between the resist pattern and the second organic insulating film to protect the second organic insulating film,

wherein the nitride etching stop film and the first and second oxide etching stop films are all provided as continuous layers with no apertures defined therein when the resist pattern is formed over the multi-layered film, and

forming an opening by an etching process using the resist pattern as a mask during at least a part of forming the opening, wherein the opening penetrates at least the first and second organic insulating films and is of substantially the same size in both the first and second organic insulating films.

Please add the following new claim:

12. (New) The method of claim 1, wherein another resist is used as a mask in enlarging the opening in the second organic insulating film but not the first organic insulating film.

REMARKS

This is in response to the Office Action dated September 12, 2002. Claims 10-11 have been canceled. New claim 12 has been added. Thus, claims 1-6, 8-9 and 12 are now pending. Attached hereto is a marked-up version of the changes made to the